

## Polar3<sup>™</sup> HiperFET<sup>™</sup> Power MOSFET

# IXFT50N60P3 IXFQ50N60P3 IXFH50N60P3

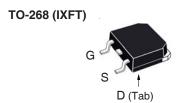
N-Channel Enhancement Mode Avalanche Rated Fast Intrinsic Rectifier



| Symbol            | Test Conditions  | Maximum R  | atings   |
|-------------------|--|------------|----------|
| V <sub>DSS</sub>  | T <sub>J</sub> = 25°C to 150°C   | 600        | V        |
| V <sub>DGR</sub>  | $T_J = 25^{\circ}C$ to 150°C, $R_{GS} = 1M\Omega$  | 600        | V        |
| $V_{\rm gss}$     | Continuous   | ± 30       | V        |
| V <sub>GSM</sub>  | Transient  | ± 40       | V        |
| I <sub>D25</sub>  | T <sub>C</sub> = 25°C  | 50         | Α        |
| I <sub>DM</sub>   | $T_{_{\rm C}}$ = 25°C, Pulse Width Limited by $T_{_{\rm JM}}$  | 125        | Α        |
| I <sub>A</sub>    | T <sub>c</sub> = 25°C  | 25         | A        |
| E <sub>AS</sub>   | $T_{c} = 25^{\circ}C$  | 1          | J        |
| dv/dt             | $I_{_{\mathrm{S}}} \leq I_{_{\mathrm{DM}}},  V_{_{\mathrm{DD}}} \leq V_{_{\mathrm{DSS}}},  T_{_{\mathrm{J}}} \leq 150^{\circ}\mathrm{C}$ | 35         | V/ns     |
| $P_{D}$           | T <sub>C</sub> = 25°C  | 1040       | W        |
| T <sub>J</sub>    |  | -55 +150   | °C       |
| $T_{JM}$          |  | 150        | °C       |
| T <sub>stg</sub>  |  | -55 +150   | °C       |
| T,                | Maximum Lead Temperature for Soldering   | 300        | °C       |
| T <sub>SOLD</sub> | Plastic Body for 10s   | 260        | °C       |
| $\mathbf{M}_{d}$  | Mounting Torque (TO-247 & TO-3P)   | 1.13 / 10  | Nm/lb.in |
| Weight            | TO-268<br>TO-3P  | 4.0<br>5.5 | g        |
|                   | TO-247   | 6.0        | g<br>g   |

| Symbol<br>(T <sub>J</sub> = 25°C U | Test Conditions Inless Otherwise Specified)         | Charac<br>Min. | teristic<br>Typ. |      |    |
|------------------------------------|---|----------------|------------------|------|----|
| BV <sub>DSS</sub>                  | $V_{GS} = 0V, I_D = 1mA$                            | 600            |                  |      | V  |
| V <sub>GS(th)</sub>                | $V_{DS} = V_{GS}, I_{D} = 4mA$                      | 3.0            |                  | 5.0  | V  |
| I <sub>GSS</sub>                   | $V_{GS} = \pm 30V, V_{DS} = 0V$                     |                |                  | ±100 | nA |
| I <sub>DSS</sub>                   | $V_{DS} = V_{DSS}, V_{GS} = 0V$                     |                |                  | 25   | μΑ |
|                                    | $T_J = 125$ °C                                      |                |                  | 2    | mA |
| R <sub>DS(on)</sub>                | $V_{GS} = 10V, I_{D} = 0.5 \bullet I_{D25}, Note 1$ |                |                  | 160  | mΩ |

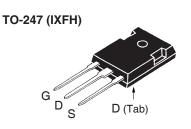
 $V_{DSS} = 600V$   $I_{D25} = 50A$   $R_{DS(on)} \le 160m\Omega$ 



TO-3P (IXFQ)

G
D
S

D (Tab)



G = Gate D = DrainS = Source Tab = Drain

#### **Features**

- Fast Intrinsic Rectifier
- Avalanche Rated
- $^{\bullet}$  Low  $\rm R_{\rm DS(ON)}$  and  $\rm Q_{\rm G}$
- Low Package Inductance

### **Advantages**

- High Power Density
- Easy to Mount
- Space Savings

## **Applications**

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

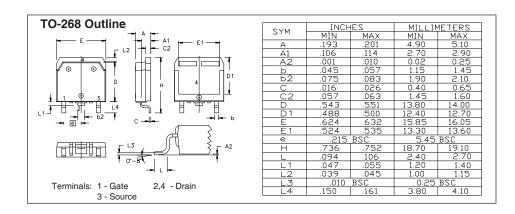


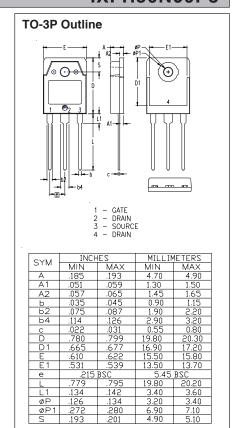
| Symbol                  | Test Conditions   | Char | acteristic | Values    |
|-------------------------|---|------|------------|-----------|
| $(T_J = 25^{\circ}C Ur$ | nless Otherwise Specified)  | Min. | Тур.       | Max.      |
| g <sub>fs</sub>         | $V_{DS} = 20V, I_{D} = 0.5 \bullet I_{D25}, Note 1$   | 32   | 55         | S         |
| C <sub>iss</sub>        |   |      | 6300       | pF        |
| C <sub>oss</sub>        | $V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$   |      | 630        | pF        |
| C <sub>rss</sub>        |   |      | 2.5        | pF        |
| R <sub>Gi</sub>         | Gate Input Resistance   |      | 1.0        | Ω         |
| t <sub>d(on)</sub>      |   |      | 31         | ns        |
| t, (                    | Resistive Switching Times   |      | 20         | ns        |
| t <sub>d(off)</sub>     | $V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_{D} = 0.5 \cdot I_{D25}$                                   |      | 62         | ns        |
| t <sub>r</sub>          | $R_{G} = 1\Omega$ (External)  |      | 17         | ns        |
| $Q_{g(on)}$             |   |      | 94         | nC        |
| Q <sub>gs</sub>         | $V_{\rm GS} = 10 \text{V},  V_{\rm DS} = 0.5 \bullet V_{\rm DSS},  I_{\rm D} = 0.5 \bullet I_{\rm D25}$ |      | 27         | nC        |
| $Q_{gd}$                |   |      | 23         | nC        |
| R <sub>thJC</sub>       |   |      |            | 0.12 °C/W |
| R <sub>thCS</sub>       | (TO-247 & TO-3P)  |      | 0.25       | °C/W      |

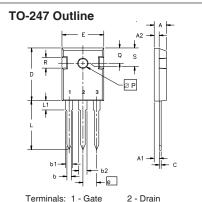
#### Source-Drain Diode

| Symbol                    | Test Conditions  | Characteristic Values |      |      |    |
|---------------------------|--|-----------------------|------|------|----|
| $(1_{J} = 25^{\circ}C U)$ | nless Otherwise Specified)   | Min.                  | Тур. | Max. |    |
| l <sub>s</sub>            | $V_{GS} = 0V$  |                       |      | 50   | A  |
| I <sub>SM</sub>           | Repetitive, Pulse Width Limited by $T_{JM}$                          |                       |      | 200  | A  |
| V <sub>SD</sub>           | $I_F = I_S$ , $V_{GS} = 0V$ , Note 1                                 |                       |      | 1.4  | V  |
| t <sub>rr</sub>           | L = 25A -di/dt = 100A/us   |                       |      | 250  | ns |
| I <sub>RM</sub>           | $I_F = 25A$ , -di/dt = 100A/ $\mu$ s<br>$V_R = 100V$ , $V_{GS} = 0V$ |                       | 11   |      | Α  |
| $\mathbf{Q}_{RM}$         | V <sub>R</sub> = 100V, V <sub>GS</sub> = 0V                          |                       | 1.1  |      | μC |

Note 1. Pulse test,  $t \le 300\mu s$ , duty cycle,  $d \le 2\%$ .





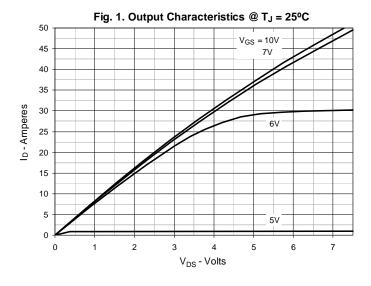


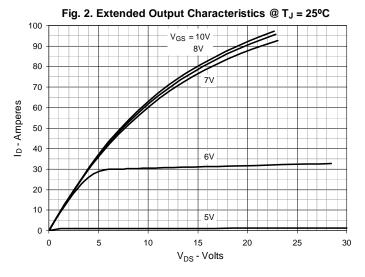
Terminals: 1 - Gate 2 - 3 - Source

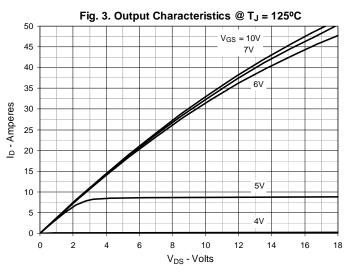
| Dim.  | Millimeter |       | Inches |       |
|-------|------------|-------|--------|-------|
|       | Min.       | Max.  | Min.   | Max.  |
| Α     | 4.7        | 5.3   | .185   | .209  |
| $A_1$ | 2.2        | 2.54  | .087   | .102  |
| $A_2$ | 2.2        | 2.6   | .059   | .098  |
| b     | 1.0        | 1.4   | .040   | .055  |
| b,    | 1.65       | 2.13  | .065   | .084  |
| b,    | 2.87       | 3.12  | .113   | .123  |
| С     | .4         | .8    | .016   | .031  |
| D     | 20.80      | 21.46 | .819   | .845  |
| Е     | 15.75      | 16.26 | .610   | .640  |
| е     | 5.20       | 5.72  | 0.205  | 0.225 |
| L     | 19.81      | 20.32 | .780   | .800  |
| L1    |            | 4.50  |        | .177  |
| ØP    | 3.55       | 3.65  | .140   | .144  |
| Q     | 5.89       | 6.40  | 0.232  | 0.252 |
| R     | 4.32       | 5.49  | .170   | .216  |
| S     | 6.15       | BSC   | 242    | BSC   |
|       |            |       |        |       |

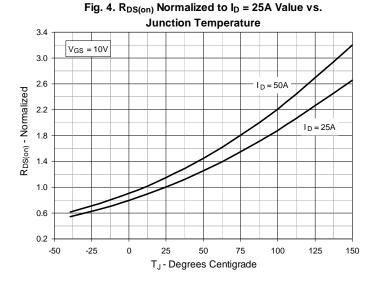
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

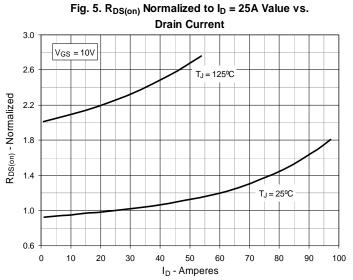


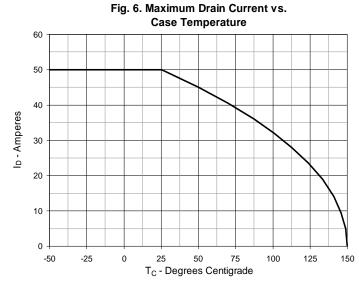












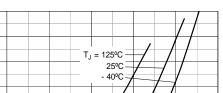


4.0

3.5

4.5

80



70 60 lo - Amperes 40 30 20 10 0

5.0 V<sub>GS</sub> - Volts

Fig. 7. Input Admittance

Fig. 8. Transconductance

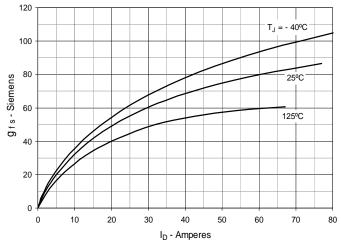


Fig. 9. Forward Voltage Drop of Intrinsic Diode

5.5

6.0

6.5

7.0

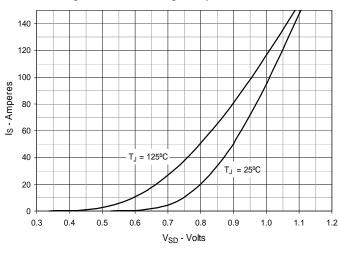


Fig. 10. Gate Charge

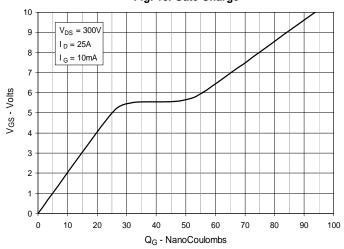


Fig. 11. Capacitance

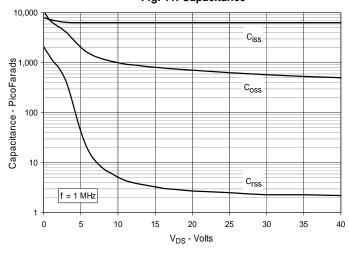
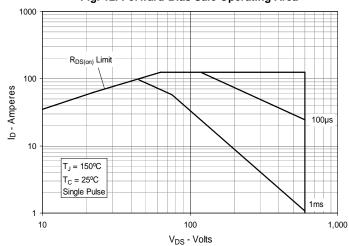


Fig. 12. Forward-Bias Safe Operating Area



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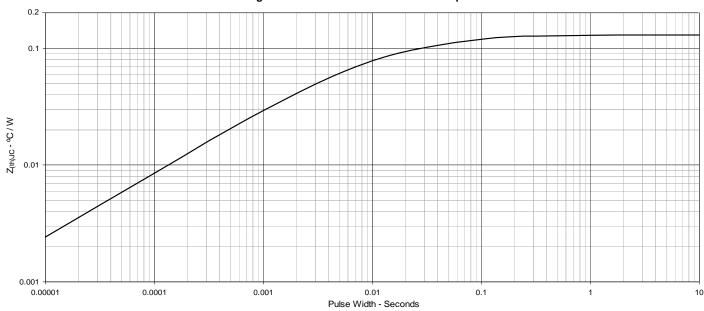


Fig. 13. Maximum Transient Thermal Impedance

